

Intermediate Silicon Tracker (INTT) Specifications

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- **1. Barrels Global Specification**
- 2. Ladder L0 Specifications
- 3. Ladder L1 (2,3) Specifications
- 4. Stave Specifications
- 5. Summary



Barrels Global Specifications

Barrels Global Configuration





Ladders and Barrels Global Specifications



	Barrel	Center of Sensor Radius (mm)	Pseudo rapidity	Quantity ladder	Angle (deg)	Coverage (ϕ) (%)	Overlap (%)	Clearance (mm)	Chips Power dissipation (W)
	0	68.76/74.62	1.03/0.97	34	0	100	2.5	0.25/1.5	56.56
Note: ← INTT barrels positions move out radially preventing interference and providing more clearance to MVTX/INTT → Number of ladders increased and it has been adjusted to maintain 100 % coverage and full hermeticities.	1	89.87/95.45	1.18/1.13	30	0	100	2.5	0.25/1.5	99.84
	2	108.35/113.61	1.03/0.99	36	0	100	2.5	0.25/1.5	119.81
	3	126.76/131.79	0.91/0.88	42	0	100	2.5	0.25/1.5	139.77
		Total Quantity: 142 Ladders: Total: 416 Watts							
	η 	α Z _{Si} - Z _{vertex} / R adder: barrel 0 BUS Extender	Radius	η = 1.0 (Silio Mo	@ Z _{verte} con S dule N	x = 10 cm Silicon Aodule	HDI	BUS	Ladder Concept Extender
	L	adder: barrels 1,2,3 BUS Extender	e HDI	Silico Mode	on ule ^I	Silicon Module	HDI	BUS	Extender
		Signa	al					Signal	4

Radiation Length of INTT Ladder



Material	Thickness [µm]	X/X _o
Silicon	320	0.34%
HDI	473	0.49%
Stave	500	0.25%
Total	1293	1.08%

HDI Material	Thickness [µm]	X/X _o
Copper*	52	0.36
Polymide	380	0.13
Total**	432	0.49

*Copper thickness is not physical thickness, but effective material thickness. **Total thickness won't become 473um, because of the effective thickness.

ны Physical and Effective Thickness of



Copper Layer

HDI composed of total 7 copper layers. 4 layers are ground or power layers, so they are solid copper, so it's 9um thickness is fully occupied by copper. On the other hand, the rest 3 layers are signal line layers where the amount of copper is a lot less than ground and power layers. Here I introduce "effective thickness" to give the correct amount of copper material for the signal layers.

One of signal layer



The copper area is only a few % of solid copper case. The effective copper thickness is calculated by 9um * a few%.

HD

Layer Structure of HDI



Sub Component Thickness Else Copper Layers Effective Real [μ [µm] Occupancy [µ m] m] Coverlay Polyide 12.5 µm Regist 20 µ/m Coverlay Glue 25 µm Copper plated 15 μm Copper plated 15 *µ* m 100% 15.00 15 L1 Electrolytic copper foil 9 *µ* m HVLINE+AGND L1 Electrolytic copper foil 9 *µ* m 100% 9.00 9 Base Polyimide 50 μm Base Polvimide 50 µm L2 Electrolytic copper foil 9 *µ* m A GND L2 Electrolytic copper foil 9 *µ* m 100% 9.00 9 Glue 25 µm 25 µm Glue Base Polyimide 12.5 µm Base Polyimide 12.5 µm Glue 15 *µ* m Glue 15 µm RF LINE L3 Electrolytic copper foil 9 µ/m L3 Electrolytic copper foil 9 μm 8.2% 0.74 9 Base Polyimide 50 µ/m Base Polyimide 50 µm L4 Electrolytic copper foil 9 µ/m PWR L4 Electrolytic copper foil 9 μm 100% 9.00 **q** Glue 25 µ/m 25 µm Glue 12.5 µm Base Polyimide 12.5 µ/m Base Polyimide Glue 15 µ/m Glue 15 µm L5 Electrolytic copper foil 9 *µ* m SIG L5 Electrolytic copper foil 9 μm 3.2% 0.29 9 50 μm Base Polyimide Base Polyimide 50 µm D GND L6 Electrolytic copper foil 9 µ/m L6 Electrolytic copper foil 9 µ m 100% 9.00 Glue 25 µm 25 µm Glue 25 µ/m Base Polyimide Base Polyimide 25 µm L7 Electrolytic copper foil 9 µ/m L7 Electrolytic copper foil 9 µ/m 0.5% 0.05 9 Copper plated 15 µm 0.08 15 Copper plated 15 µ/m 15 Regist 20 µ/m Coverlay Glue 25 µm Coverlay Polyimide 12.5 µm μm Glue for support plate 40 µ m 438 μm Support Plate FR-4 1.0t 1000 µm TOTAL厚 438 µ m TOTAL厚 473 µ ⊓ Total 50.140 ~ ~

1	i otal	02.140	93	380	
	Radiation Length [cm]	1.435		28.6	Total
	X/Xrad [%]	0.36339	0	.132867	0.496254

12.5

25

50

25

15

50

25

15

50

25

25

25

12.5

000

12.5

12.5

7



Ladder L0 Specifications

Ladder LO: Sensor Specifications



SPHENIX

Ladder LO: HDI and Chips Specifications



Thickness: 473 um Width: 25.5 mm z-length total: 300 mm (radiation length = 0.49%)

Sensor thickness: 320 um FPHX chip thickness: 320 um





Ladder L1 (2, 3) Specifications

Ladder L1 (2,3): Sensor Specifications



SPHENIX

Ladder L1 (2,3): HDI Specifications



Thickness: 473 um Width: 38.0 mm z-length total: 400 mm (radiation length = 0.49%)

Sensor thickness: 320 um FPHX chip thickness: 320 um





Stave Specifications

Ladder LO: Stave Specifications





Ladder L1 (2,3): Stave Specifications







Summary

Summary: Silicon sensors and HDI are fabricated already

Mechanical support: CFC stave



Gluing/wire-bonding HDI/Chips/Testing



INTT telescope for the beam test: 120 GeV at FNAL

Gluing/wire-bonding Sensors/Chips



SPHENIX

Three half ladders (barrels 1, 2 and 3)





